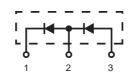


DSEE30-12A

HiPerFRED[™] Epitaxial Diode

I _{FAV}	=	30 A
V _{RRM}	=	1200 V [®]
t _{rr}	=	30 ns

V _{RRM} ① V	V _{RRM} V	Туре
1200	600	DSEE30-12A



Symbol	Conditions	Maximum	Ratings
IFRMS		60	A
I _{FAVM} ①	$T_c = 90^{\circ}C$; rectangular, d = 0.5	30	A
I _{FSM}	$T_{vJ} = 45^{\circ}C$; $t_p = 10$ ms (50 Hz), sine	200	А
E _{AS}	$T_{vJ} = 25^{\circ}C$; non-repetitive $I_{AS} = 1.3 A$; L = 180 µH	0.2	mJ
I _{AR}	$V_A = 1.5$ V_R typ.; f = 10 kHz; repetitive	0.1	A
T _{vj}		-55+175	°C
T _{VJM}		175	°C
T _{stg}		-55+150	°C
TL	1.6 mm (0.063 in) from case for 10 s	260	°C
P _{tot}	$T_c = 25^{\circ}C$	165	W
M _d	Mounting Torque	0.9/6	Nm/lb.in.
Weight	typical	2	g

Symbol	Conditions	Characteristic Valu typ. max.		
I _R [⊕] ②	$T_{VJ} = 25^{\circ}C V_{R} = V_{RRM}$ $T_{VJ} = 150^{\circ}C V_{R} = V_{RRM}$		200 2	μA mA
V _F ³	$I_F = 30 \text{ A};$ $T_{VJ} = 125^{\circ}\text{C}$ $T_{VJ} = 25^{\circ}\text{C}$		1.75 2.5	V V
R _{thJC} R _{thCH}		0.25	0.9	K/W K/W
t _{rr}	$I_F = 1 \text{ A}; \text{ -di/dt} = 200 \text{ A/}\mu\text{s};$ $V_R = 30 \text{ V}$	30		ns
I _{RM}	$V_{\rm R}$ = 100 V; $~I_{\rm F}$ = 50 A; -di_{\rm F}/dt = 100 A/µs $T_{\rm vJ}$ = 100°C	4		A

Notes: Data given for $T_{VJ} = 25^{\circ}C$ and per diode unless otherwise specified \odot Diodes connected in series

- \bigcirc Pulse test: pulse Width = 5 ms, Duty Cycle < 2.0 %
- 3 Pulse test: pulse Width = $300 \ \mu$ s, Duty Cycle < $2.0 \ \%$

IXYS reserves the right to change limits, test conditions and dimensions.

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TO-247 AD

Features

- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM} -values
- · Soft recovery behaviour
- Epoxy meets UL 94V-0

Applications

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

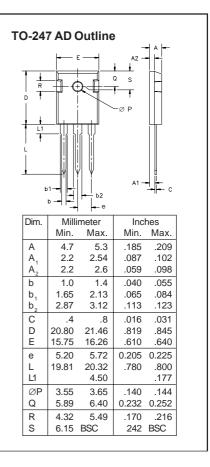
Advantages

- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
 Low I_{RM} reduces:
 - Power dissipation within the diode
- Turn-on loss in the commutating switch

Notes

• Please see DSEP 30-06A Data Sheet for characteristic curves.

DSEE30-12A



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
	4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	

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